# **3-to-8 Line Decoder**

The MC74VHC138 is an advanced high speed CMOS 3-to-8 decoder fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

When the device is enabled, three Binary Select inputs (A0 - A2) determine which one of the outputs  $(\overline{Y0} - \overline{Y7})$  will go Low. When enable input E3 is held Low or either  $\overline{E2}$  or  $\overline{E1}$  is held High, decoding function is inhibited and all outputs go high. E3,  $\overline{E2}$ , and  $\overline{E1}$  inputs are provided to ease cascade connection and for use as an address decoder for memory systems.

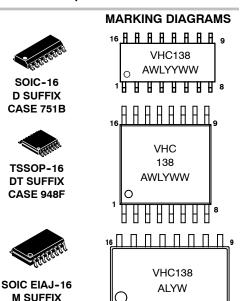
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed:  $t_{PD} = 5.7 \text{ns}$  (Typ) at  $V_{CC} = 5 \text{V}$
- Low Power Dissipation:  $I_{CC} = 4\mu A$  (Max) at  $T_A = 25$ °C
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: V<sub>OLP</sub> = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- Chip Complexity: 122 FETs or 30.5 Equivalent Gates
- These devices are available in Pb-free package(s). Specifications herein
  apply to both standard and Pb-free devices. Please see our website at
  www.onsemi.com for specific Pb-free orderable part numbers, or
  contact your local ON Semiconductor sales office or representative.



#### **ON Semiconductor**

http://onsemi.com



A = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week

**CASE 966** 

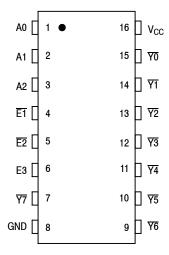
= Assembly Location A = Assembly Location

WL = Wafer Lot L = Wafer Lot Y = Year Y = Year WW = Work Week W = Work Week

#### **ORDERING INFORMATION**

Device	Package	Shipping
MC74VHC138D	SOIC-16	48 Units/Rail
MC74VHC138DR2	SOIC-16	2500 Units/Reel
MC74VHC138DT	TSSOP-16	96 Units/Rail
MC74VHC138DTR2	TSSOP-16	2500 Units/Reel
MC74VHC138M	SOIC EIAJ-16	48 Units/Rail
MC74VHC138MEL	SOIC EIAJ-16	2000 Units/Reel

## **PIN ASSIGNMENT**



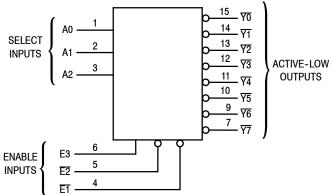
## **FUNCTION TABLE**

Inputs							Ou	tput	S				
E3	E2	E1	A2	<b>A</b> 1	Α0	Y0	<b>Y</b> 1	Y2	<b>Y3</b>	<b>Y</b> 4	Y5	Y6	<b>Y</b> 7
Х	Х	Н	Х	Χ	Χ	Η	Н	Н	Н	Н	Н	Н	Н
X	Н	Χ	X	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
L	Χ	Χ	Х	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н
Н	L	L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н
Н	L	L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	Н
Н	L	L	Н	L	L	Н	Н	Н	Н	L	Н	Н	Н
Н	L	L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н
Н	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	Н
Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L

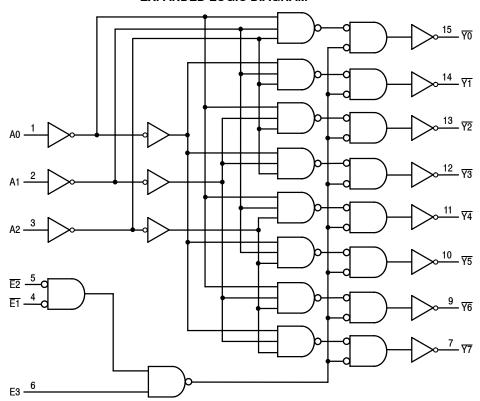
H = high level (steady state); L = low level (steady state);

X = don't care

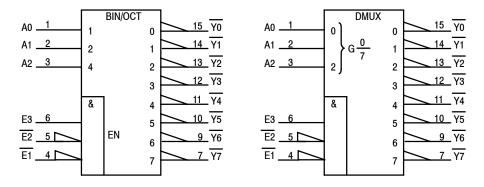
# LOGIC DIAGRAM



## **EXPANDED LOGIC DIAGRAM**



## **IEC LOGIC DIAGRAM**



#### **MAXIMUM RATINGS\***

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage		- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage		- 0.5 to + 7.0	٧
V <sub>out</sub>	DC Output Voltage		$-$ 0.5 to $V_{CC}$ + 0.5	V
I <sub>IK</sub>	Input Diode Current		- 20	mA
lok	Output Diode Current		± 20	mA
l <sub>out</sub>	DC Output Current, per Pin		± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GNE	) Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		– 65 to + 150	°C

<sup>\*</sup> Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		2.0	5.5	V
V <sub>in</sub>	DC Input Voltage		0	5.5	V
V <sub>out</sub>	DC Output Voltage		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature		- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>		3.3V ±0.3V 5.0V ±0.5V	0	100 20	ns/V

The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

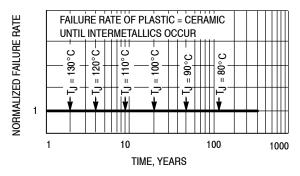


Figure 1. Failure Rate vs. Time Junction Temperature

<sup>†</sup>Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>		T <sub>A</sub> = 25°C	;	T <sub>A</sub> = ≤	85°C	<b>T</b> <sub>A</sub> = ≤	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		-
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	-
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μΑ
Icc	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0		40.0	μΑ

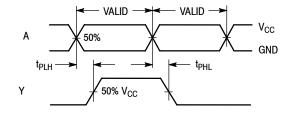
## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$ )

Symbo	T <sub>A</sub> = 25°C		;	T <sub>A</sub> = - 40 to 85°C		T <sub>A</sub> = - 55 to 125°C					
ı	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		8.2 10.0	11.4 15.8	1.0 1.0	13.5 18.0	1.0 1.0	13.5 18.0	ns
	A to Y	$V_{CC} = 5.0 \pm 0.5V$	$C_L = 15pF$ $C_L = 50pF$		5.7 7.2	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		8.1 10.6	12.8 16.3	1.0 1.0	15.0 18.5	1.0 1.0	15.0 18.5	ns
	E3 to Y	$V_{CC} = 5.0 \pm 0.5V$	$C_L = 15pF$ $C_L = 50pF$		5.6 7.1	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		8.2 10.7	11.4 14.9	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
	E2 or E1 to Y	$V_{CC} = 5.0 \pm 0.5V$	$C_L = 15pF$ $C_L = 50pF$		5.8 7.3	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
C <sub>IN</sub>	Maximum Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
$C_{PD}$	Power Dissipation Capacitance (Note 1)	34	рF

<sup>1.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## **SWITCHING WAVEFORMS**



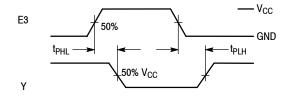
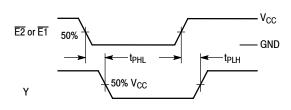
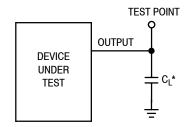


Figure 2.

Figure 3.







\*Includes all probe and jig capacitance

Figure 5. Test Circuit

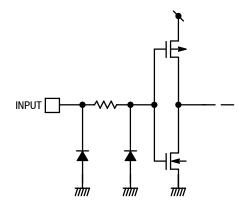
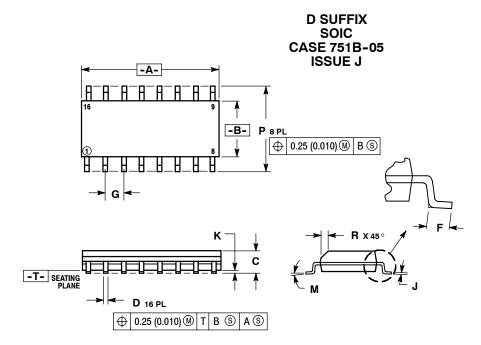


Figure 6. Input Equivalent Circuit

#### PACKAGE DIMENSIONS

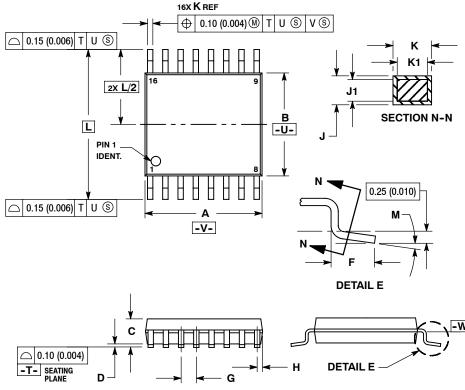


#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006)
  PER SIDE.
  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

## **DT SUFFIX TSSOP CASE 948F-01 ISSUE 0**



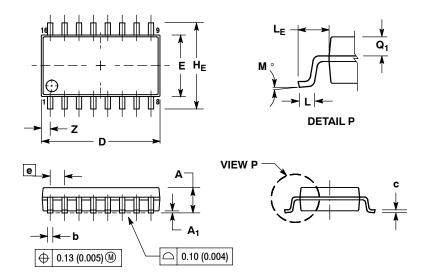
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- 7/14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD FLASH.
  PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252	BSC	
M	0°	8°	0°	8°	

#### PACKAGE DIMENSIONS

#### **M SUFFIX SOIC EIAJ-16 CASE 966-01 ISSUE O**



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

  DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
Ŀ	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.78		0.031

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